

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VHB10-12F is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CB0}	36 V
V_{CEO}	18 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	20 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	8.8 °C/W

PACKAGE STYLE .380 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10712

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 15 mA	18			V
BV_{CES}	I _C = 50 mA	36			V
BV_{EBO}	I _E = 2.5 mA	4.0			V
I_{CB0}	V _{CB} = 12.5 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 250 mA	5.0		200	---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz			45	pF
P_G η_c	V _{CC} = 12.5 V P _{OUT} = 10 W f = 175 MHz	10	60		dB %